UNA0222 (UN222)

Silicon PNP epitaxial planar type (3 elements) Silicon NPN epitaxial planar type (3 elements)

For motor drives

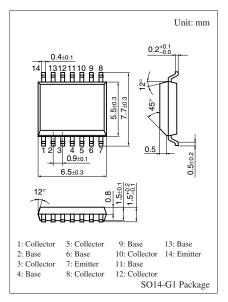
■ Features

- Small and lightweight
- Low power consumption (low V_{CE(sat)} transistor used)
- Low voltage drive
- Transistors with built-in resistor with 6 elements incorporated

■ Absolute Maximum Ratings $T_a = 25$ °C

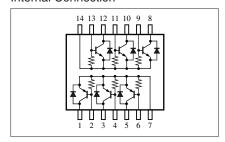
Parameter		Symbol	Rating	Unit	
PNP	Collector-base voltage (Emitter open)	V _{CBO}	-10	V	
	Collector-emitter voltage (Base open)	V _{CEO}	-10	V	
	Collector current	I_C	-3	A	
	Peak collector current	I_{CP}	-4	A	
NPN	Collector-base voltage (Emitter open)	V _{CBO}	10	V	
	Collector-emitter voltage (Base open)	V _{CEO}	10	V	
	Collector current	I_C	3	A	
	Peak collector current	I_{CP}	4	A	
Overall	Total power dissipation *	P_{T}	0.5	W	
	Junction temperature	T_{j}	150	°C	
	Storage temperature	T_{stg}	-55 to +150	°C	

Note) *: When the dissipation on one device is $T_C = 25^{\circ}C$



Marking Symbol: UN222

Internal Connection



\blacksquare Electrical Characteristics T_a = $25^{\circ}C \pm 3^{\circ}C$

• PNP

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \ \mu A, I_E = 0$	-10			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-10			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -6 \text{ V}, I_{E} = 0$			-1	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = -1 \text{ V}, I_{C} = -0.5 \text{ A}$	200		700	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -2 \text{ A}, I_B = -50 \text{ mA}$			- 0.45	V
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		70		pF
(Common base, input open circuited)						
Forward voltage *1	V _F	$I_F = -1 A$			-1.5	V
Bias resistance *2	R _{EB}		-30%	10	+30%	kΩ

• NPN

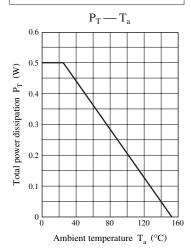
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	10			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	10			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 6 \text{ V}, I_{E} = 0$			1	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = 1 \text{ V}, I_{C} = 0.5 \text{ A}$	200		700	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 2 \text{ A}, I_B = 50 \text{ mA}$			0.25	V
Transition frequency	f_T	$V_{CB} = 6 \text{ V}, I_{E} = -50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		50		pF
(Common base, input open circuited)						
Forward voltage *1	V _F	$I_F = 1 A$			1.5	V
Bias resistance *2	R _{EB}		-30%	10	+30%	kΩ

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

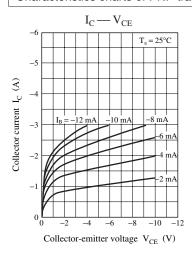
^{2. *1:} Application to the built-in diode

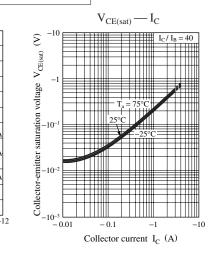
^{*2:} Application to the built-in resistance

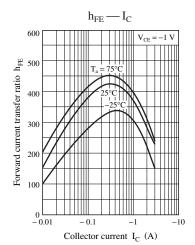
Common characteristics chart

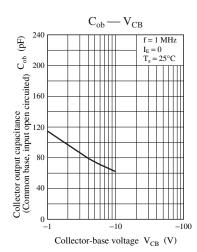


Characteristics charts of PNP transistor block

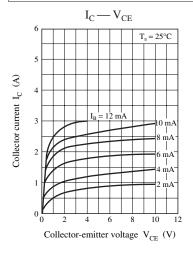


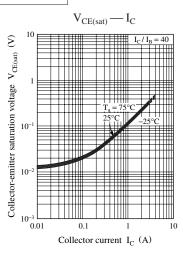


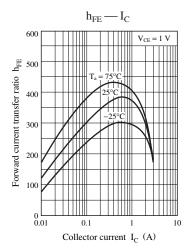


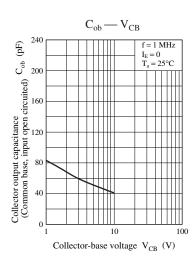


Characteristics charts of NPN transistor block









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